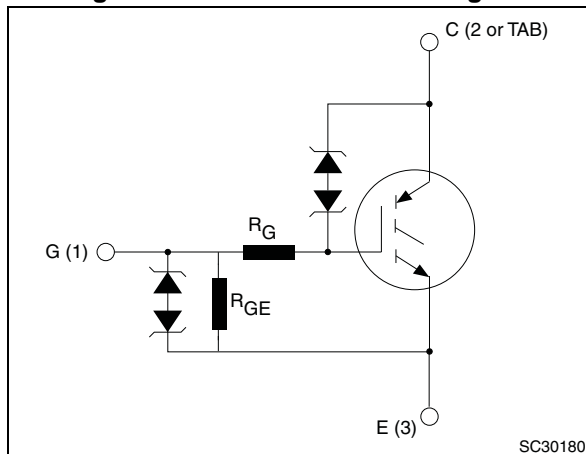


Figure 1. Internal schematic diagram



### Features

- Designed for automotive applications and AEC-Q101 qualified
- Low threshold voltage
- Low on-voltage drop
- High voltage clamping feature
- Logic level gate charge
- ESD gate-emitter protection
- Gate and gate-emitter integrated resistors

### Application

- Automotive ignition

### Description

This application specific IGBT utilizes the most advanced PowerMESH™ technology. The built-in Zener diodes between gate-collector and gate-emitter provide overvoltage protection capabilities. The device also exhibits low on-state voltage drop and low threshold drive for use in automotive ignition system.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STGB35N35LZ-1	GB35N35LZ	I <sup>2</sup> PAK	Tube
STGB35N35LZT4	GB35N35LZ	D <sup>2</sup> PAK	Tape and reel
STGP35N35LZ	GP35N35LZ	TO-220	Tube

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
2.1	Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuits</b> .....	<b>9</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>10</b>
<b>5</b>	<b>Packaging mechanical data</b> .....	<b>15</b>
<b>6</b>	<b>Revision history</b> .....	<b>17</b>



# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage ( $V_{GE} = 0$ )	$V_{CES}$ (clamped)	V
$V_{ECS}$	Emitter collector voltage ( $V_{GE} = 0$ )	20	V
$I_C^{(1)}$	Continuous collector current at $T_C = 25\text{ °C}$	40	A
$I_C^{(1)}$	Continuous collector current at $T_C = 100\text{ °C}$	30	A
$I_{CP}^{(2)}$	Pulsed collector current	80	A
$V_{GE}$	Gate-emitter voltage	$V_{GE}$ (clamped)	V
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	176	W
$E_{AS}$	Single pulse energy ( $T_C=25\text{ °C}$ , $L=1.6\text{ mH}$ , $I_C = 22\text{ A}$ , $V_{CC} = 50\text{ V}$ )	450	mJ
ESD	Human body model ( $R=1,5\text{ k}\Omega$ , $C=100\text{ pF}$ )	8	kV
	Machine model ( $R=0$ , $C=100\text{ pF}$ )	800	V
	Charged device model	2	kV
$T_{stg}$	Storage temperature	- 55 to 175	°C
$T_j$	Operating junction temperature		

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

2. Pulse width limited by maximum junction temperature

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.85	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	°C/W

## 2 Electrical characteristics

( $T_j = 25\text{ °C}$  unless otherwise specified)

**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{CES(\text{clamped})}$	Collector emitter clamped voltage ( $V_{GE}=0$ )	$I_C=2\text{ mA}$ ,		345		V
		$I_C=2\text{ mA}$ , $T_j = -40\text{ °C to }150\text{ °C}$	320		380	V
$V_{(BR)ECS}$	Emitter collector break-down voltage ( $V_{GE}=0$ )	$I_C = 75\text{ mA}$	20	28		V
$V_{GE(\text{clamped})}$	Gate emitter clamped voltage	$I_G = \pm 2\text{ mA}$	12	14	16	V
$I_{CES}$	Collector cut-off current ( $V_{GE} = 0$ )	$V_{CE} = 15\text{ V}$ , $T_j = 150\text{ °C}$			10	$\mu\text{A}$
		$V_{CE} = 200\text{ V}$ , $T_j = 150\text{ °C}$			100	$\mu\text{A}$
$I_{GES}$	Gate-emitter leakage current ( $V_{CE} = 0$ )	$V_{GE} = \pm 10\text{ V}$	500	625	830	$\mu\text{A}$
$R_{GE}$	Gate emitter resistance		12	15	20	$\text{k}\Omega$
$R_G$	Gate resistance			1.5		$\text{k}\Omega$
$V_{GE(\text{th})}$	Gate threshold voltage	$V_{CE} = V_{GE}$ , $I_C = 1\text{ mA}$ , $T_j = -40\text{ °C}$	1.4			V
		$V_{CE} = V_{GE}$ , $I_C = 1\text{ mA}$	1.2	1.6	2.3	V
		$V_{CE} = V_{GE}$ , $I_C = 1\text{ mA}$ , $T_j = 150\text{ °C}$	0.7			V
$V_{CE(\text{sat})}$	Collector-emitter saturation voltage	$V_{GE} = 4.5\text{ V}$ , $I_C = 10\text{ A}$		1.15	1.5	V
		$V_{GE} = 4.5\text{ V}$ , $I_C = 15\text{ A}$		1.3	1.7	V

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GE} = 0$	-	700	-	pF
$C_{oes}$	Output capacitance		-	150	-	pF
$C_{res}$	Reverse transfer capacitance		-	6	-	pF
$Q_g$	Gate charge	$V_{CE} = 280\text{ V}$ , $I_C = 15\text{ A}$ , $V_{GE} = 5\text{ V}$	-	49	-	nC

Table 6. Functional characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
U.I.S.	Functional test open secondary coil	$R_G = 0$ , $T_j = 150\text{ °C}$ , $V_{CC} = 50\text{ V}$ , $V_{GE} = 5\text{ V}$ , $L = 1.6\text{ mH}$	18	-	-	A

Table 7. Switching time

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Resistive load Turn-on delay time Rise time	$V_{CC} = 14\text{ V}$ , $R_L = 1\text{ }\Omega$ , $V_{GE} = 5\text{ V}$	-	1.1 7	-	$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
$t_{d(on)}$ $t_r$	Resistive load Turn-on delay time Rise time	$V_{CC} = 14\text{ V}$ , $R_L = 1\text{ }\Omega$ , $V_{GE} = 5\text{ V}$ $T_j = 150\text{ °C}$	-	1 6.6	-	$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
$t_{d(off)}$ $t_f$ $dv/dt$	Inductive load Turn-off delay time Fall time Turn-off voltage slope	$V_{CC} = 300\text{ V}$ , $L = 1\text{ mH}$ $I_C = 15\text{ A}$ , $V_{GE} = 5\text{ V}$	-	26.5 5.5 70	-	$\mu\text{s}$ $\mu\text{s}$ $\text{V}/\mu\text{s}$
$t_{d(off)}$ $t_f$ $dv/dt$	Inductive load Turn-off delay time Fall time Turn-off voltage slope	$V_{CC} = 300\text{ V}$ , $L = 1\text{ mH}$ $I_C = 15\text{ A}$ , $V_{GE} = 5\text{ V}$ $T_j = 150\text{ °C}$	-	28 9 65	-	$\mu\text{s}$ $\mu\text{s}$ $\text{V}/\mu\text{s}$

## 2.1 Electrical characteristics (curves)

Figure 2. Collector-emitter saturation voltage vs temperature

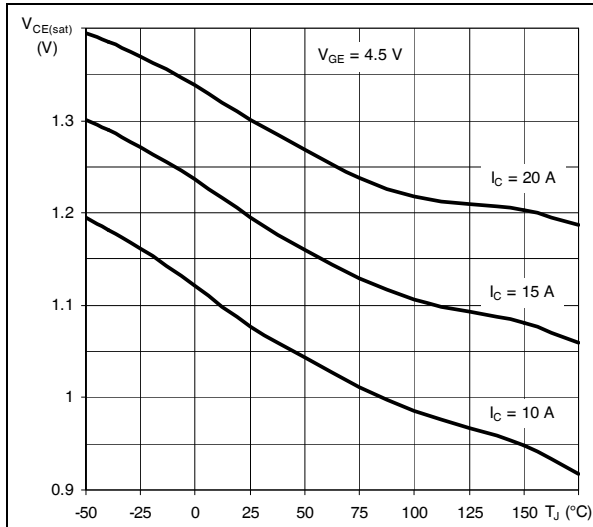


Figure 3. Self clamped inductive switch

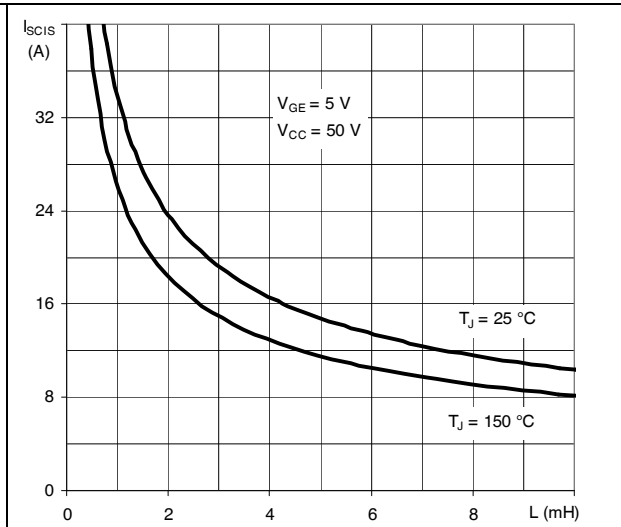


Figure 4. Output characteristics ( $T_J = 25^{\circ}C$ )

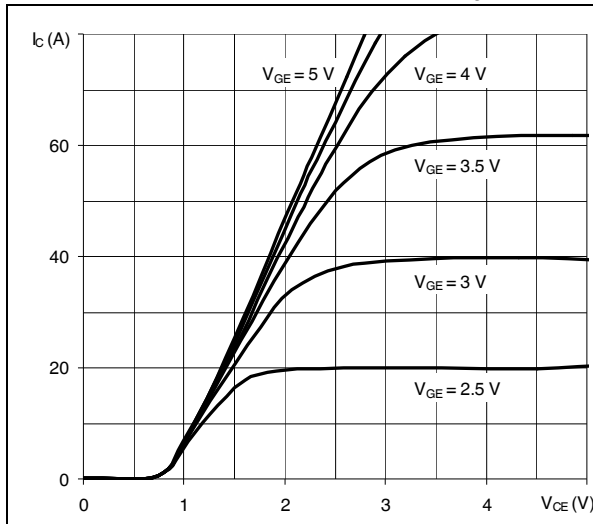


Figure 5. Output characteristics ( $T_J = -40^{\circ}C$ )

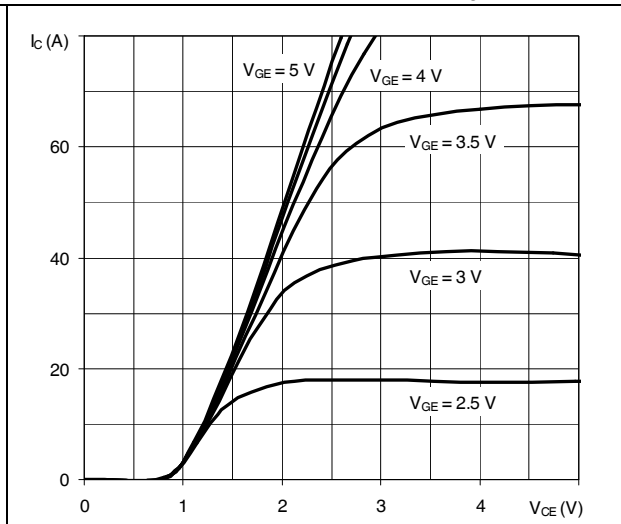


Figure 6. Output characteristics ( $T_J = 175\text{ }^\circ\text{C}$ )

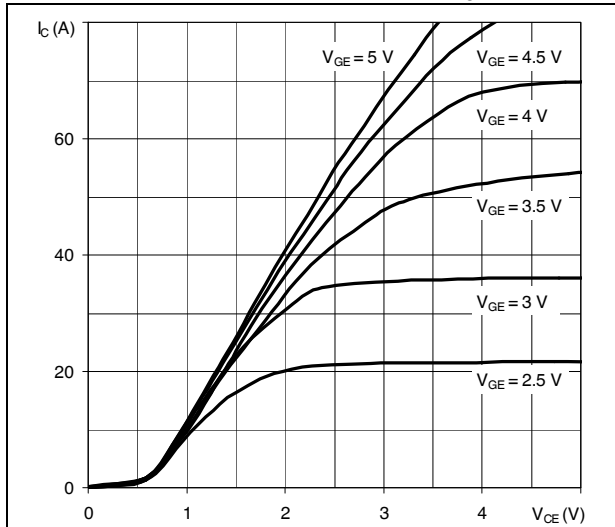


Figure 7. Transfer characteristics

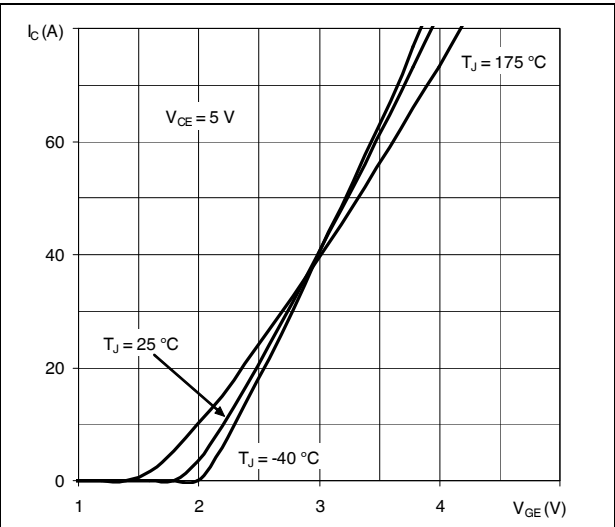


Figure 8. Collector cut-off current vs temperature

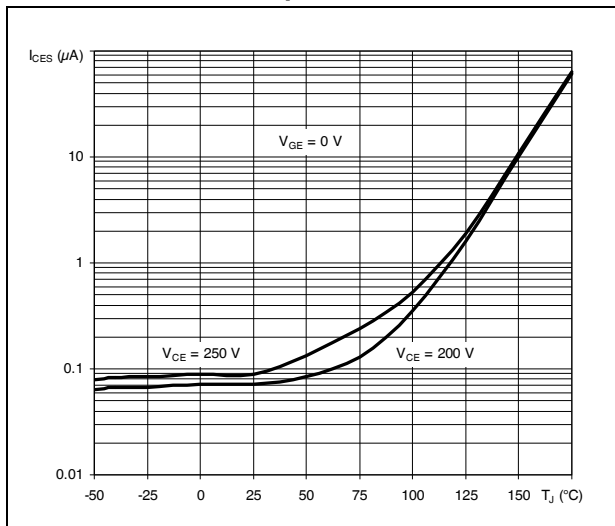


Figure 9. Normalized collector emitter voltage vs temperature

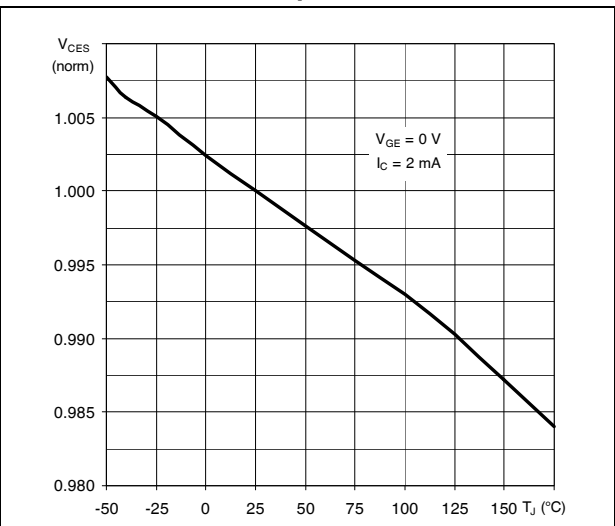


Figure 10. Normalized gate threshold voltage vs temperature

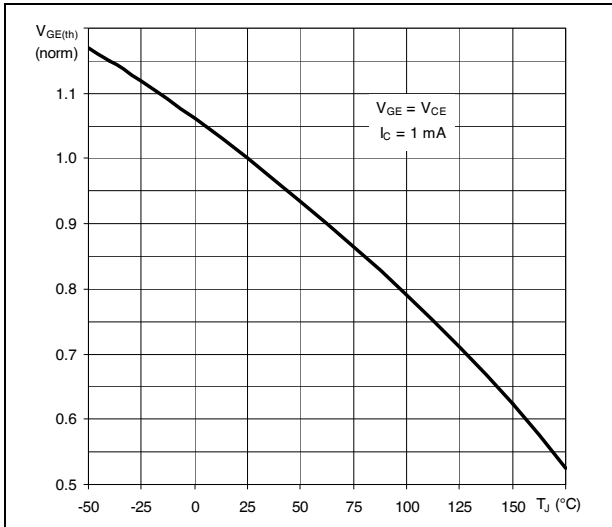


Figure 11. Gate charge

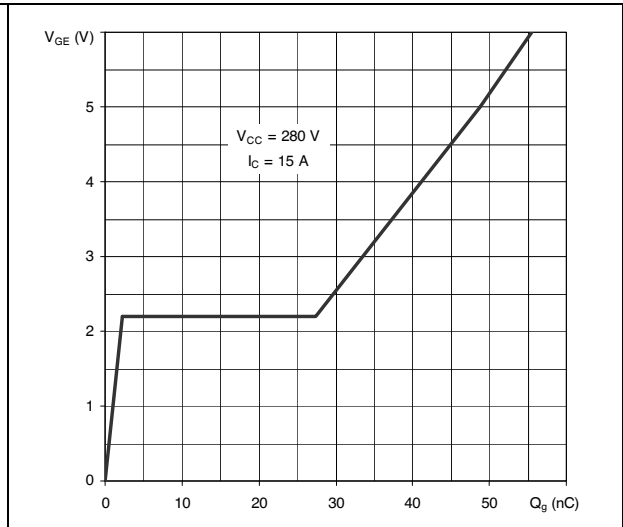
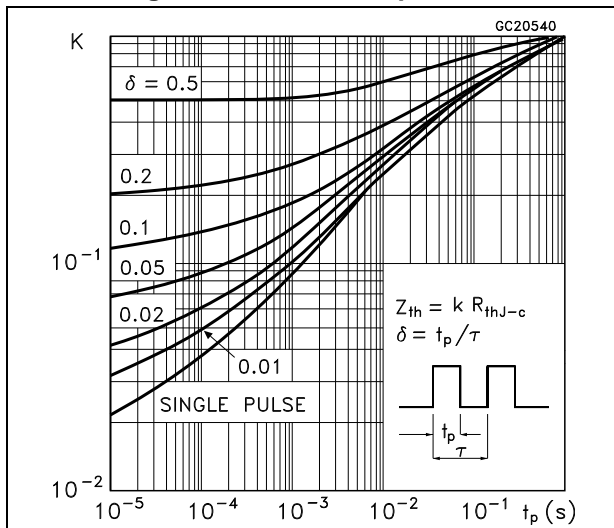


Figure 12. Thermal impedance





### 3 Test circuits

Figure 13. Test circuit for inductive load switching



Figure 14. Gate charge test circuit

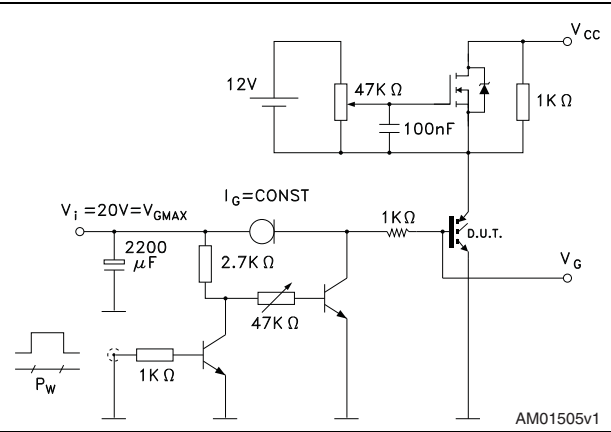
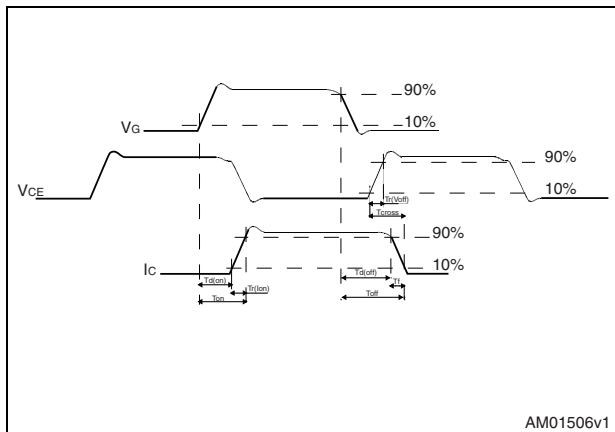


Figure 15. Switching waveform



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**Table 8. D<sup>2</sup>PAK (TO-263) mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 16. D<sup>2</sup>PAK (TO-263) drawing

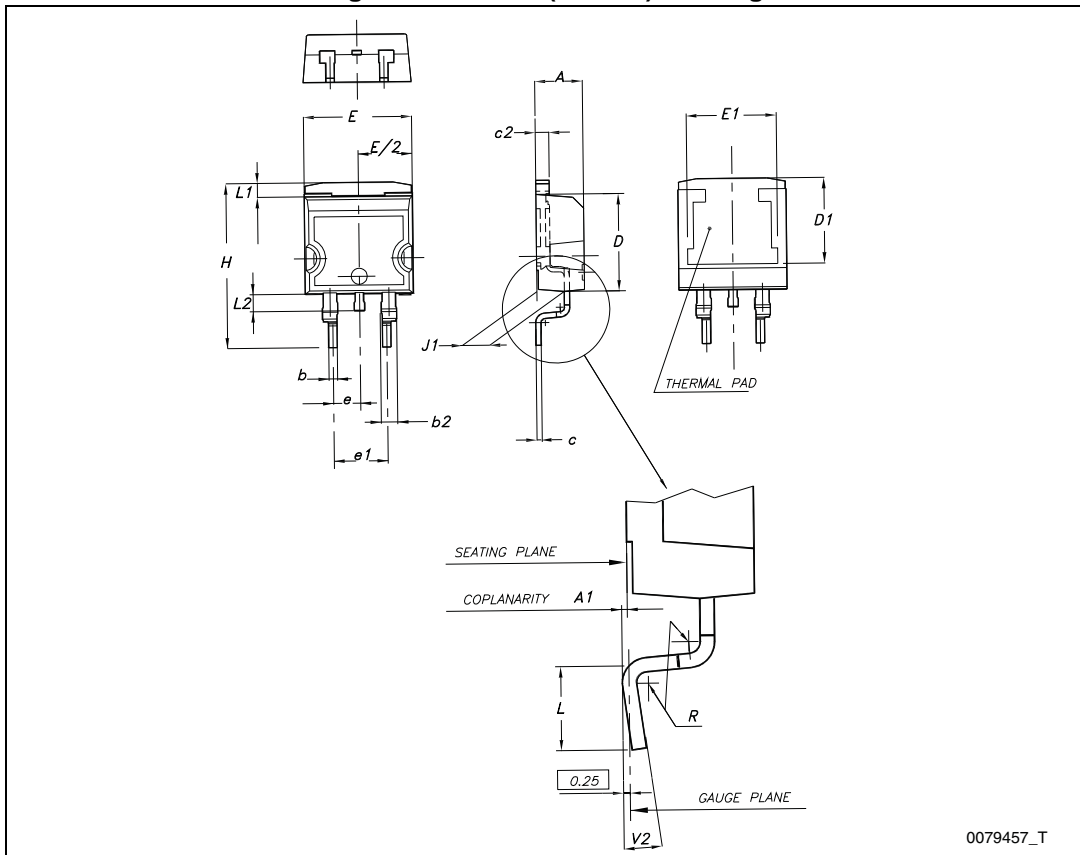
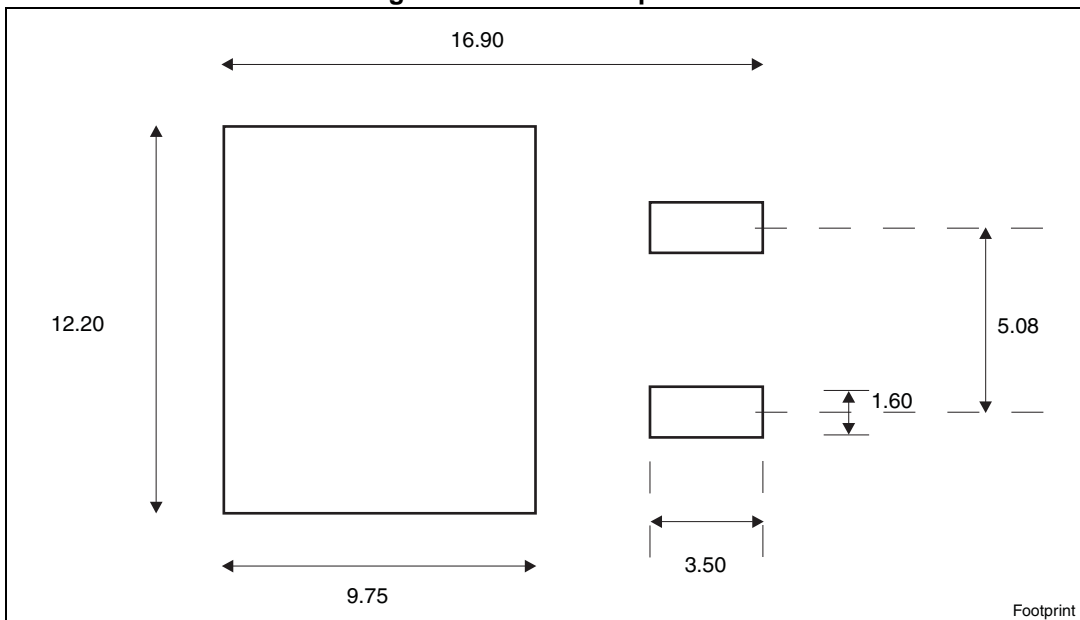


Figure 17. D<sup>2</sup>PAK footprint<sup>(a)</sup>



a. All dimension are in millimeters

Table 9. I<sup>2</sup>PAK (TO-262) mechanical data

DIM.	mm.		
	min.	typ	max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

Figure 18. I<sup>2</sup>PAK (TO-262) drawing

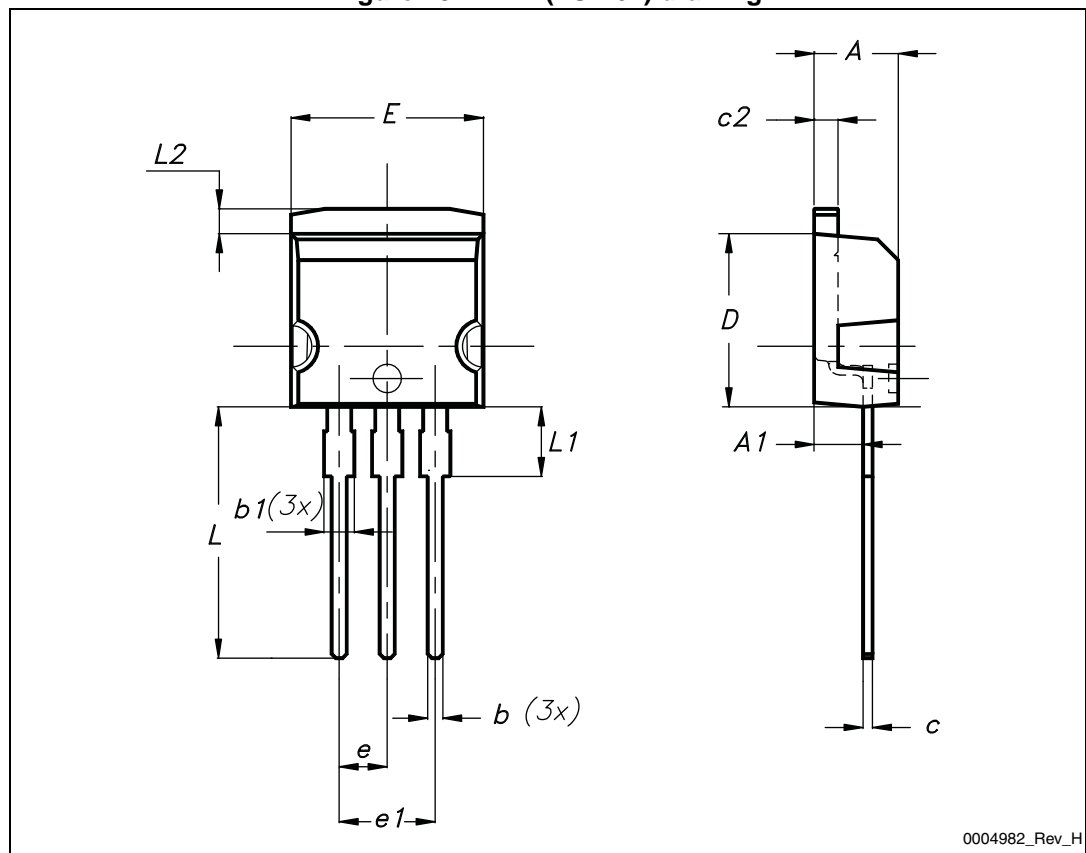
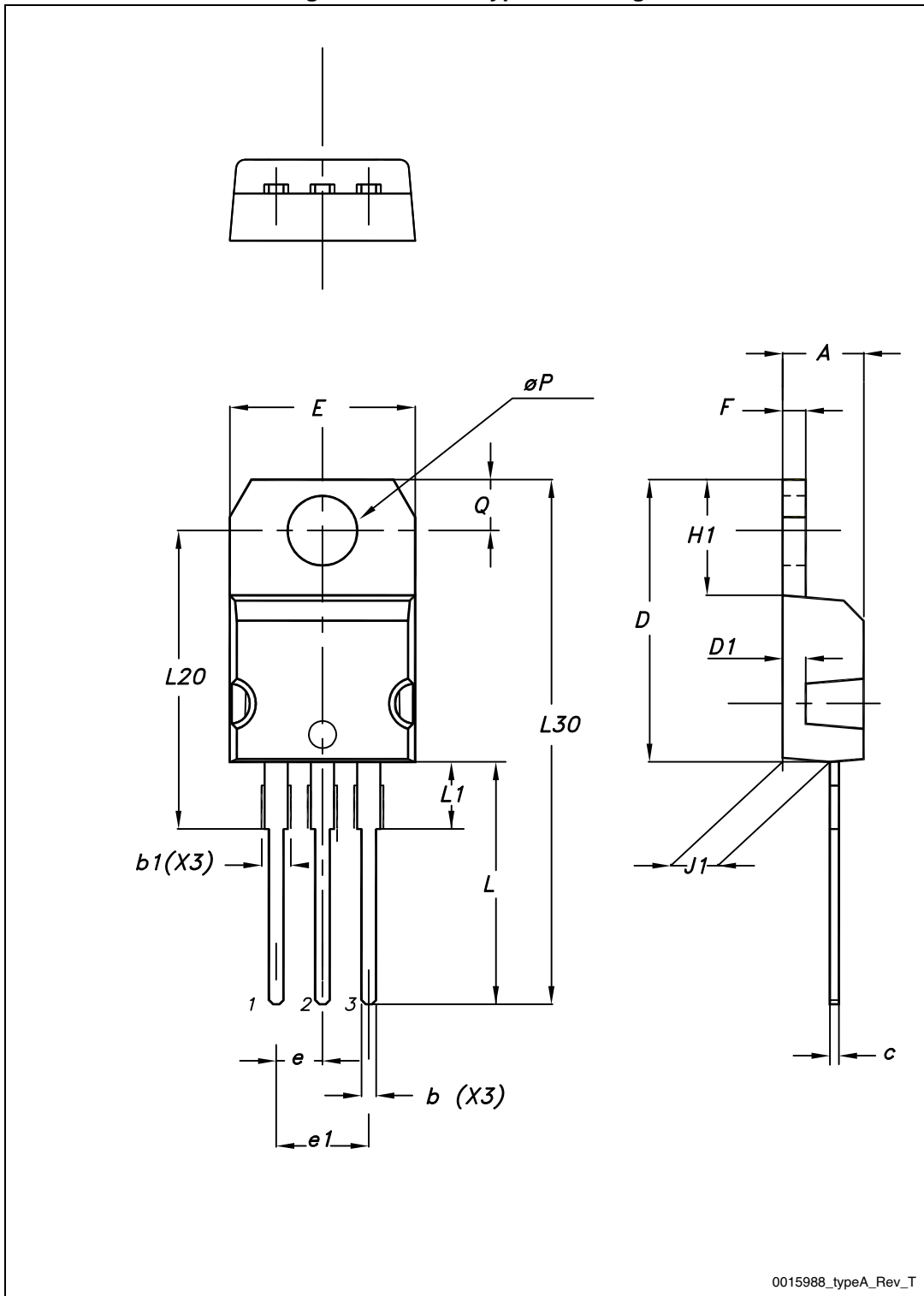


Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 19. TO-220 type A drawing



## 5 Packaging mechanical data

Table 11. D<sup>2</sup>PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 20. Tape for D<sup>2</sup>PAK (TO-263)

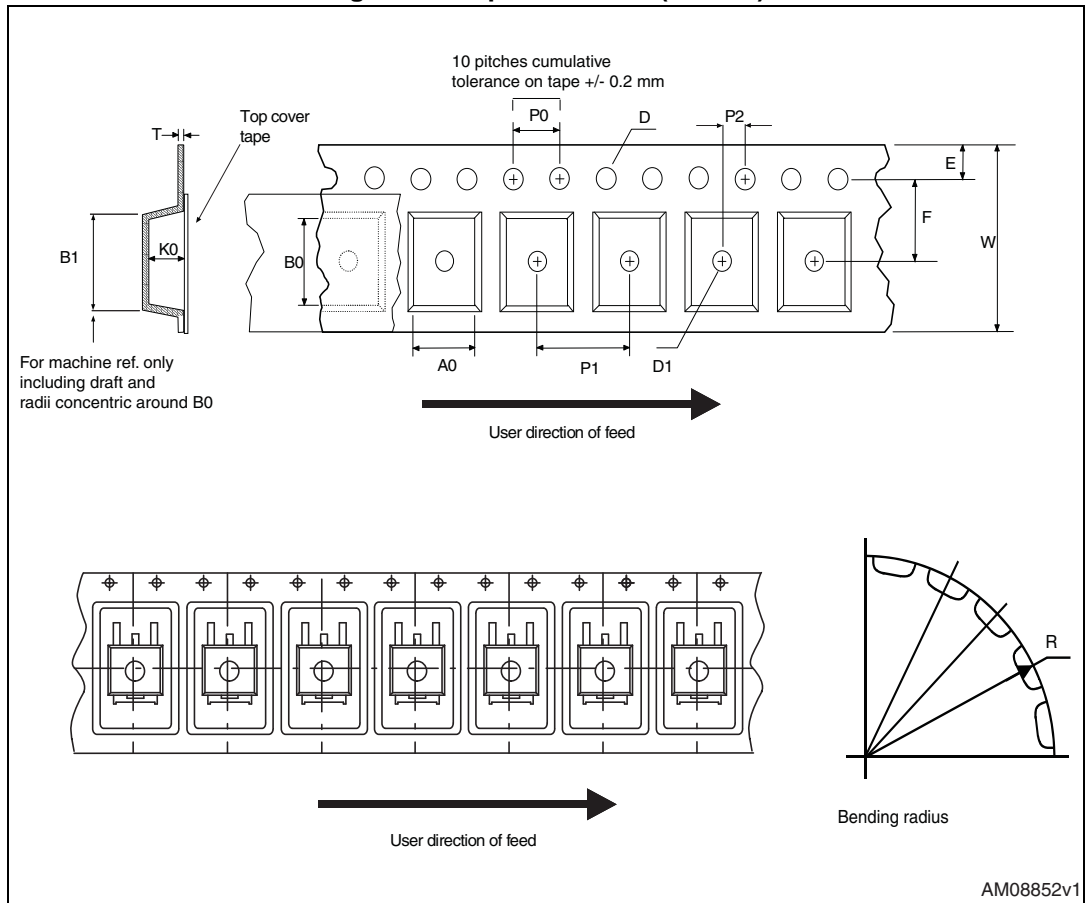
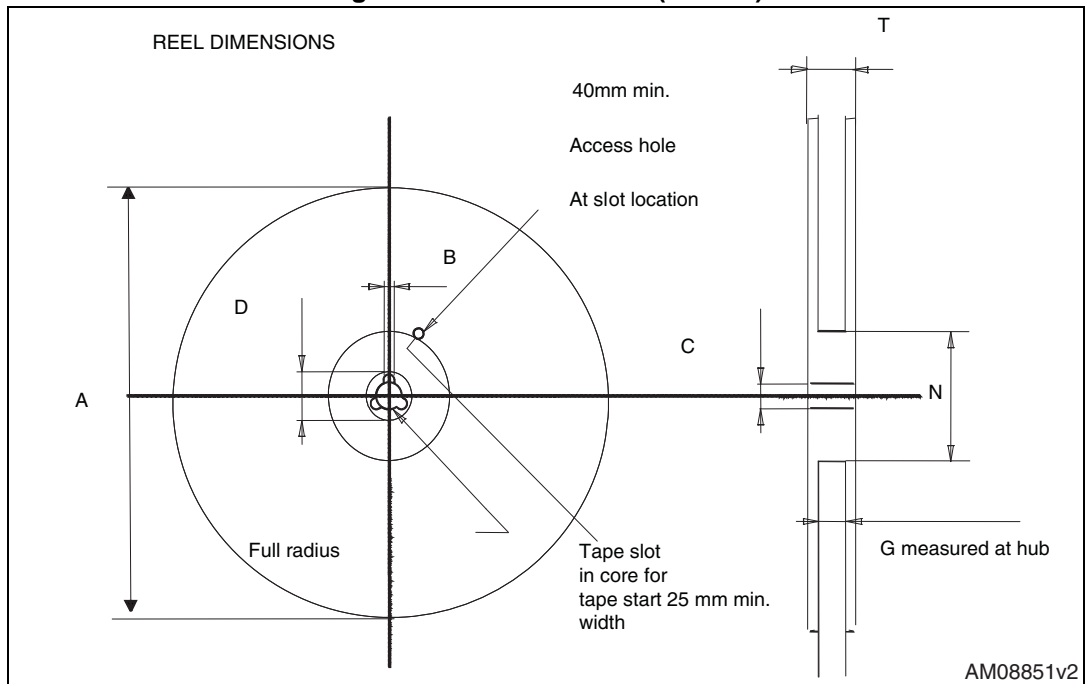


Figure 21. Reel for D<sup>2</sup>PAK (TO-263)





## 6 Revision history

Table 12. Document revision history

Date	Revision	Changes
29-Mar-2006	1	Initial release.
03-Jun-2009	2	Document status promoted from preliminary data to datasheet.
05-Nov-2009	3	Inserted <a href="#">Chapter 2.1: Electrical characteristics (curves)</a>
16-Feb-2010	4	Added new package, mechanical data: TO-220
03-Jun-2010	5	<ul style="list-style-type: none"><li>– Added <a href="#">Figure 12: Thermal impedance</a></li><li>– Modified <a href="#">Figure 4</a>, <a href="#">Figure 5</a>, <a href="#">Figure 6</a> and <a href="#">Figure 7</a></li><li>– D<sup>2</sup>PAK mechanical data has been updated</li></ul>
28-May-2013	6	<ul style="list-style-type: none"><li>– Updated title in cover page, <a href="#">Chapter 5: Packaging mechanical data</a> and <a href="#">Chapter 5: Packaging mechanical data</a>.</li></ul>

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